

IN THE SPECIFICATION:

Page 7, please delete the paragraph beginning at line 19 to the bottom of the page and insert the following:

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The principle of the design of a projection exposure machine 1 is described below with the aid of figure 1. The projection exposure machine 1 has an illuminating device 2 and a projection lens 3. The projection lens 3 comprises a lens arrangement 4 with a multiplicity of lenses and an aperture stop 5. The lenses 4a are arranged along an optical axis 6. A mask or reticle 7, which is held in the beam path by means of a mask holder 8, is arranged between the illuminating device 2 and the projection lens 3. The mask 7 is imaged on an image plane 9 by means of the projection lens 3 by a clearly reduced factor. Such masks 7 used in microlithography have a micrometer or nanometer structure which is imaged on the image plane 13 by means of the projection lens 3 in a fashion reduced in size down to a factor of 10, in particular the factor 4. The minimum structures which can still be resolved depend on the wavelength (of the light used for the illumination, and on the aperture of the aperture stop 5, the maximum achievable resolution of the projection exposure machine rising with decrease in the wavelength of the

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